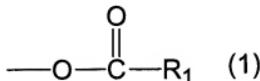


Amendments to the Claims:

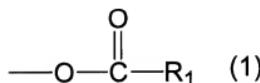
The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An underlayer coating forming composition comprising a dextrin ester compound ~~that wherein~~ at least 50% of hydroxy groups in ~~the~~ dextrin ~~is~~ are converted into ester groups of formula (1):



wherein R₁ is C₁₋₁₀alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C₁₋₆alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, a crosslinking compound, and an organic solvent.

2. (Currently Amended) An underlayer coating forming composition comprising a dextrin ester compound ~~that wherein~~ at least 50% of hydroxy groups in ~~the~~ dextrin ~~is~~ are converted into ester groups of formula (1):



wherein R₁ is C₁₋₁₀alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C₁₋₆alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine

atom or C₁₋₆alkoxycarbonyl group has the same meaning as that defined in claim 1, and that
wherein the dextrin ester compound has a weight average molecular weight of 4000 to 20000,
and wherein the composition further comprises a crosslinking compound, and an organic
solvent.

3. (Previously Presented) The underlayer coating forming composition according to claim 1, further comprising an acid compound or an acid generator.

4. (Currently Amended) A method for forming a photoresist pattern for use in
manufacture of a semiconductor device, comprising the steps of:

_____ coating the underlayer coating forming composition according to claim 1 on a
semiconductor substrate, and baking it to form an underlayer coating;

_____ forming a photoresist layer on the underlayer coating;

_____ exposing the semiconductor substrate covered with the underlayer coating and
the photoresist layer to light; and

_____ developing the photoresist layer after the exposure to light.

5. (Currently Amended) The underlayer coating forming composition according to claim 1, in whichwherein the composition is used for forming an underlayer coating by
coating the composition on a semiconductor substrate having a hole with an aspect ratio
shown in height/diameter of 1 or more, and baking it.

6. (Previously Presented) The underlayer coating forming composition according to claim 2, further comprising an acid compound or an acid generator.

7. (Currently Amended) A method for forming a photoresist pattern for use in
manufacture of a semiconductor device, comprising the steps of:

_____ coating the underlayer coating forming composition according to claim 2 on a
semiconductor substrate, and baking it to form an underlayer coating;

_____ forming a photoresist layer on the underlayer coating;
_____ exposing the semiconductor substrate covered with the underlayer coating and
the photoresist layer to light; and
_____ developing the photoresist layer after the exposure to light.

8. (Currently Amended) A method for forming a photoresist pattern for use in
manufacture of a semiconductor device, comprising ~~the steps of~~:

_____ coating the underlayer coating forming composition according to claim 3 on a
semiconductor substrate, and baking it to form an underlayer coating;
_____ forming a photoresist layer on the underlayer coating;
_____ exposing the semiconductor substrate covered with the underlayer coating and
the photoresist layer to light; and
_____ developing the photoresist layer after the exposure to light.

9. (Currently Amended) The underlayer coating forming composition according
to claim 2, ~~in which~~wherein the composition is used for forming an underlayer coating by
coating the composition on a semiconductor substrate having a hole with an aspect ratio
shown in height/diameter of 1 or more, and baking it.

10. (Currently Amended) A method for forming a photoresist pattern for use in
manufacture of a semiconductor device, comprising ~~the steps of~~:

_____ coating the underlayer coating forming composition according to claim 6 on a
semiconductor substrate, and baking it to form an underlayer coating;
_____ forming a photoresist layer on the underlayer coating;
_____ exposing the semiconductor substrate covered with the underlayer coating and
the photoresist layer to light; and
_____ developing the photoresist layer after the exposure to light.